



News Release

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Elpida Memory Completes Development of Next-Generation 512 Megabit DDR3 SDRAM for High-Performance Computing

*Newly Developed DRAM Device Offers Twice the Speed of DDR2,
First to Utilize "Dual Gate" Transistor Technology*

TOKYO, JAPAN, August 23, 2005—Elpida Memory, Inc. (Elpida), Japan's leading global supplier of Dynamic Random Access Memory (DRAM), today announced the development of 512 Megabit DDR3 SDRAM—the next-generation memory for computing applications such as notebooks, desktop PCs and servers. The new DDR3 architecture will feature high-speed data transfer of up to 1333 Megabits per second (Mbps), double the speed of the DDR2 architecture currently in volume production.

To achieve simultaneous high-speed operation with low-power consumption, Elpida has incorporated "dual-gate" transistor technology. This technology suppresses the leakage current in the DRAM device—an unwanted side effect that occurs when pursuing low-voltage operation while maintaining or improving transistor performance. The "dual-gate" transistor has recently been used for high-performance processors; however, this is its first use within a DRAM device.

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“The goal when developing next-generation DDR3 memory is for it to maintain the benefits of DDR2, such as low-voltage operation, while significantly boosting the speed,” said Jun Kitano, director of Technical Marketing for Elpida Memory (USA). “Our use of “dual gate” transistors—a first in DRAM—will allow our new 512 Megabit DDR3 device to achieve the high-performance operation that will be critical for future advanced computing applications.”

Next-Generation Memory: DDR3 SDRAM

In addition to the significant increase in data transfer, the 512 Megabit DDR3 SDRAM device will also provide improved power consumption—1.5 Volt vs. the 1.8 Volt operation that is currently available in DDR2 architecture. A newly introduced automatic calibration feature for the output buffer will enhance the ability to control the system timing budget during variations in voltage and temperature. This feature helps enable robust, high-performance operation—one of the key benefits of DDR3 architecture.

Elpida’s 512 Megabit DDR3 SDRAM will also utilize 90 nm process technology. Elpida has already established volume production at 90 nm which, in turn, will allow production on the newly developed DDR3 devices to be ramped as necessary to satisfy market demand.

Availability

Elpida’s 512 Megabit DDR3 device is expected to ship as customer samples by the end of 2005. Initial production is anticipated for 2006 in accordance with market demand. Elpida also plans to develop higher density DDR3 products such as 1 Gigabit and 2 Gigabit.

About Elpida Memory, Inc.

Elpida Memory, Inc. is a manufacturer of Dynamic Random Access Memory (DRAM) silicon chips with headquarters based in Tokyo, Japan, and sales and marketing operations located in Japan, North America, Europe and Asia. Elpida’s state-of-the-art semiconductor wafer manufacturing facilities are located in Hiroshima, Japan. Elpida offers a broad range of leading-edge DRAM products for high-end servers, mobile phones, digital television sets and digital cameras as well as personal computers. Elpida had sales of ¥207.0 billion during the fiscal year ending March 31, 2005. For more information, visit www.elpida.com.

The information contained within this news release, is current as of the date of release. Please note that the information herein may be revised later without prior notice.